Andreev reflection in s-type superconductor proximized 3D topological insulator. Supplemental Material.

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DIFFERENTIAL RESISTANCE IN A WIDE BIAS RANGE

In all N-TI-S devices studied the differential resistance, \( R_{\text{diff}} \), behaves similarly to the reference N-TI-N device and exhibits no AR related features. This is verified in Figs. 1a and 1b for two representative devices in a wide bias range. Just like in the reference N-TI-N device, see Fig. 1c, the small zero bias feature in \( B = 0 \) develops into a pronounced resistance peak in a magnetic field \( B \sim 1 \text{ T} \). This behavior is qualitatively consistent with a scenario of competing quantum corrections, weak anti-localization and Altshuler-Aronov, among which the former is suppressed by a perpendicular magnetic field and both are suppressed by a high bias owing to dephasing, see, e.g. Ref.\(^1\).

![Differential resistance in N-TI-S devices s2 (a) and s3 (b) and reference N-TI-N device n (c). The data is taken simultaneously with the main text noise data in Fig. 3 (s2), Fig. 4 (s3) and Fig. 2 (n).](image)

ELECTRON-PHONON ENERGY RELAXATION

As discussed in the main text, at large biases, \(|V| > 0.8 \text{ mV}\), the data deviate below the \( q = e \) fit, both in zero and finite \( B \)-field, which is a result of shot noise suppression via electron-phonon (\( e-ph \)) energy relaxation\(^2,3\). We have checked that for \( T_N > 5 \text{ K} \) the \( e-ph \) cooling dominates the noise response and is consistent with the linear dependence \( P_J \propto T_N^\alpha - T^\alpha \), where \( P_J \) is the total dissipated Joule heat power and the exponent varies between \( \alpha \approx 3 \) and \( \alpha \approx 4 \) in different devices, see Fig. 2. A cooling rate of this type might
arise from the interaction with two-dimensional (e.g., surface) acoustic phonons\textsuperscript{4,5}, similar to graphene\textsuperscript{6–8}, or the interplay of \textit{e-ph} and impurity scattering\textsuperscript{9}. Note, that the doping dependence of the surface electrons’ cooling rate in 3D TI\textsuperscript{10} Bi\textsubscript{2}Se\textsubscript{3} at much higher $T$ is consistent with the relaxation via surface acoustic phonons.

FIG. 2. E-ph energy relaxation in the strongly non-equilibrium transport regime. Close to linear dependence $T_N^\kappa \propto P_J$ at bath temperatures of $T = 0.6 \text{ K}$ (blue curves) and $T = 4.2 \text{ K}$ (red curves) in devices s1(a), s2(b), n(d) and at bath temperature of $T = 0.6 \text{ K}$ at zero (blue curve) and nonzero (green curve) magnetic field in device s3(c).